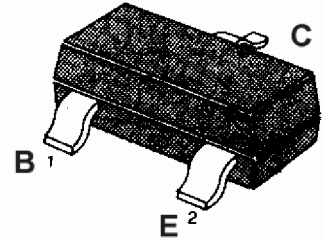


APPLICATION: Low Frequency Amplifier and High Frequency OSC.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_c	150	mA
Collector Power Dissipation	P_c	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55~150	$^\circ\text{C}$

SOT-23


1.Base 2.Emmitter 3.Collector

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	60				$V_{CE}=6V, I_c=1mA$
Collector Cut-off Current	I_{CBO}			0.1	μA	$V_{CB}=60V, I_E=0$
Emitter Cut-off Current	I_{EBO}			0.1	μA	$V_{EB}=5V, I_c=0$
Collector-Base Breakdown Voltage	BV_{CBO}	60			V	$I_c=0.1mA, I_E=0$
Collector-Emmitter Breakdown Voltage	BV_{CEO}	50			V	$I_c=1mA, I_B=0$
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	$I_E=0.1mA, I_c=0$
Base-Emmitter Voltage	V_{BE}	0.55	0.62	0.65	V	$V_{CE}=6V, I_c=1mA$
Collector-Emmitter Saturation Voltage	$V_{CE(sat)}$		0.15	0.3	V	$I_c=100mA, I_B=10mA$
Base-Emmitter Saturation Voltage	$V_{BE(sat)}$		0.86	1	V	$I_c=100mA, I_B=10mA$
Gain bandwidth product	f_t	150	250		MHz	$I_c=10mA, V_{CE}=6V$
Common Base Output Capacitance	C_{ob}			3.5	PF	$V_{CB}=6V, I_E=0, f=1MHz$

 h_{FE} Classification And Marking

Print Mark	L3	L4	L5	L6	L7	L8	L9
Classification	L3	L4	L5	L6	L7	L8	L9
h_{FE}	60~120	90~180	135~270	200~400	400~600	600~1000	>1000